MUN2115, MMUN2115L, MUN5115, DTA114TE, DTA114TM3, NSBA114TF3

Digital Transistors (BRT) R1 = 10 kΩ, R2 = ∞ kΩ

PNP Transistors with Monolithic Bias Resistor Network

This series of digital transistors is designed to replace a single device and its external resistor bias network. The Bias Resistor Transistor (BRT) contains a single transistor with a monolithic bias network consisting of two resistors; a series base resistor and a base−emitter resistor. The BRT eliminates these individual components by integrating them into a single device. The use of a BRT can reduce both system cost and board space.

Features

- Simplifies Circuit Design
- Reduces Board Space
- Reduces Component Count
- S and NSV Prefix for Automotive and Other Applications Requiring Unique Site and Control Change Requirements; AEC-Q101 Qualified and PPAP Capable
- These Devices are Pb−Free, Halogen Free/BFR Free and are RoHS Compliant

MAXIMUM RATINGS (T_A = 25°C)

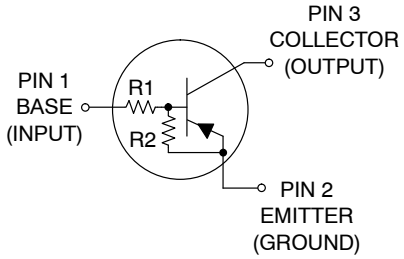
Rating	Symbol	Max	Unit
Collector−Base Voltage	V_{CBO}	50	Vdc
Collector−Emitter Voltage	V_{CEO}	50	Vdc
Collector Current − Continuous	I_C	100	mAdc
Input Forward Voltage	$V_{IN(fwd)}$	40	Vdc
Input Reverse Voltage	$V_{IN(rev)}$	5	Vdc

Stresses exceeding those listed in the Maximum Ratings table may damage the device. If any of these limits are exceeded, device functionality should not be assumed, damage may occur and reliability may be affected.

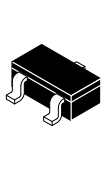
ON Semiconductor®

www.onsemi.com

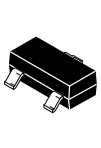
PIN CONNECTIONS



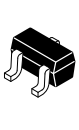
MARKING DIAGRAMS



SC−59
CASE 318D
STYLE 1



SOT−23
CASE 318
STYLE 6



SC−70/SOT−323
CASE 419
STYLE 3



SC−75
CASE 463
STYLE 1



SOT−723
CASE 631AA
STYLE 1



SOT−1123
CASE 524AA
STYLE 1

XXX = Specific Device Code
M = Date Code*
▪ = Pb−Free Package

(Note: Microdot may be in either location)

*Date Code orientation may vary depending upon manufacturing location.

ORDERING INFORMATION

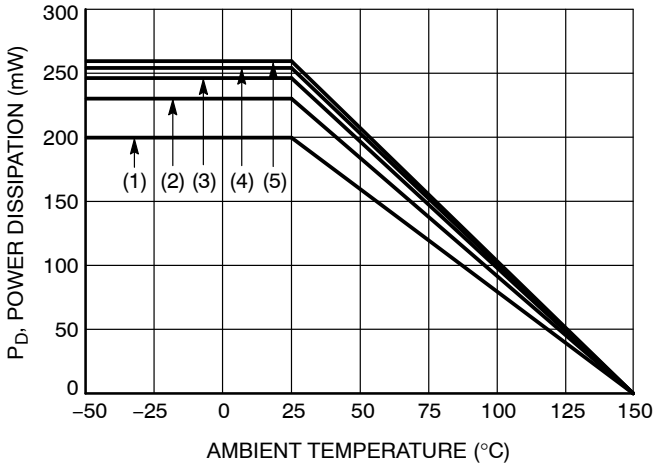
See detailed ordering, marking, and shipping information in the package dimensions section on page 2 of this data sheet.

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Table 1. ORDERING INFORMATION

Device	Part Marking	Package	Shipping†
MUN2115T1G	6E	SC−59 (Pb−Free)	3000 / Tape & Reel
MMUN2115LT1G	A6E	SOT−23 (Pb−Free)	3000 / Tape & Reel
MUN5115T1G, SMUN5115T1G	6E	SC−70/SOT−323 (Pb−Free)	3000 / Tape & Reel
DTA114TET1G	6E	SC−75 (Pb−Free)	3000 / Tape & Reel
DTA114TM3T5G	6E	SOT−723 (Pb−Free)	8000 / Tape & Reel
NSBA114TF3T5G	L (90°)*	SOT−1123 (Pb−Free)	8000 / Tape & Reel

†For information on tape and reel specifications, including part orientation and tape sizes, please refer to our Tape and Reel Packaging Specifications Brochure, BRD8011/D.
* (xx°) = Degree rotation in the clockwise direction.



(1) SC−75 and SC−70/SOT−323; Minimum Pad
(2) SC−59; Minimum Pad
(3) SOT−23; Minimum Pad
(4) SOT−1123; 100 mm^2, 1 oz. copper trace
(5) SOT−723; Minimum Pad

Figure 1. Derating Curve

Table 2. THERMAL CHARACTERISTICS

Characteristic	Symbol	Max	Unit
THERMAL CHARACTERISTICS (SC−59) (MUN2115)			
Total Device Dissipation T_A = 25°C (Note 1) (Note 2) Derate above 25°C (Note 1) (Note 2)	P_D	 230 338 1.8 2.7	 mW mW/°C
Thermal Resistance, Junction to Ambient (Note 1) (Note 2)	$R_{\theta JA}$	540 370	°C/W
Thermal Resistance, Junction to Lead (Note 1) (Note 2)	$R_{\theta JL}$	264 287	°C/W
Junction and Storage Temperature Range	T_J, T_{stg}	−55 to +150	°C
THERMAL CHARACTERISTICS (SOT−23) (MMUN2115L)			
Total Device Dissipation T_A = 25°C (Note 1) (Note 2) Derate above 25°C (Note 1) (Note 2)	P_D	 246 400 2.0 3.2	 mW mW/°C
Thermal Resistance, Junction to Ambient (Note 1) (Note 2)	$R_{\theta JA}$	508 311	°C/W
Thermal Resistance, Junction to Lead (Note 1) (Note 2)	$R_{\theta JL}$	174 208	°C/W
Junction and Storage Temperature Range	T_J, T_{stg}	−55 to +150	°C
THERMAL CHARACTERISTICS (SC−70/SOT−323) (MUN5115)			
Total Device Dissipation T_A = 25°C (Note 1) (Note 2) Derate above 25°C (Note 1) (Note 2)	P_D	 202 310 1.6 2.5	 mW mW/°C
Thermal Resistance, Junction to Ambient (Note 1) (Note 2)	$R_{\theta JA}$	618 403	°C/W
Thermal Resistance, Junction to Lead (Note 1) (Note 2)	$R_{\theta JL}$	280 332	°C/W
Junction and Storage Temperature Range	T_J, T_{stg}	−55 to +150	°C
THERMAL CHARACTERISTICS (SC−75) (DTA114TE)			
Total Device Dissipation T_A = 25°C (Note 1) (Note 2) Derate above 25°C (Note 1) (Note 2)	P_D	 200 300 1.6 2.4	 mW mW/°C
Thermal Resistance, Junction to Ambient (Note 1) (Note 2)	$R_{\theta JA}$	600 400	°C/W
Junction and Storage Temperature Range	T_J, T_{stg}	−55 to +150	°C
THERMAL CHARACTERISTICS (SOT−723) (DTA114TM3)			
Total Device Dissipation T_A = 25°C (Note 1) (Note 2) Derate above 25°C (Note 1) (Note 2)	P_D	 260 600 2.0 4.8	 mW mW/°C
Thermal Resistance, Junction to Ambient (Note 1) (Note 2)	$R_{\theta JA}$	480 205	°C/W
Junction and Storage Temperature Range	T_J, T_{stg}	−55 to +150	°C

1. FR−4 @ Minimum Pad.
2. FR−4 @ 1.0 x 1.0 Inch Pad.
3. FR−4 @ 100 mm^2, 1 oz. copper traces, still air.
4. FR−4 @ 500 mm^2, 1 oz. copper traces, still air.

Table 2. THERMAL CHARACTERISTICS

Characteristic	Symbol	Max	Unit
THERMAL CHARACTERISTICS (SOT−1123) (NSBA114TF3)			
Total Device Dissipation T_A = 25°C (Note 3) (Note 4) Derate above 25°C (Note 3) (Note 4)	P_D	 254 297 2.0 2.4	 mW mW/°C
Thermal Resistance, (Note 3) Junction to Ambient (Note 4)	$R_{\theta JA}$	493 421	°C/W
Thermal Resistance, Junction to Lead (Note 3)	$R_{\theta JL}$	193	°C/W
Junction and Storage Temperature Range	T_J, T_{stg}	−55 to +150	°C

1. FR−4 @ Minimum Pad.
2. FR−4 @ 1.0 x 1.0 Inch Pad.
3. FR−4 @ 100 mm^2, 1 oz. copper traces, still air.
4. FR−4 @ 500 mm^2, 1 oz. copper traces, still air.

Table 3. ELECTRICAL CHARACTERISTICS (T_A = 25°C, unless otherwise noted)

Characteristic	Symbol	Min	Typ	Max	Unit
OFF CHARACTERISTICS					
Collector−Base Cutoff Current (V_{CB} = 50 V, I_E = 0)	I_{CBO}	–	–	100	nAdc
Collector−Emitter Cutoff Current (V_{CE} = 50 V, I_B = 0)	I_{CEO}	–	–	500	nAdc
Emitter−Base Cutoff Current (V_{EB} = 6.0 V, I_C = 0)	I_{EBO}	–	–	0.9	mAdc
Collector−Base Breakdown Voltage (I_C = 10 μA, I_E = 0)	$V_{(BR)CBO}$	50	–	–	Vdc
Collector−Emitter Breakdown Voltage (Note 5) (I_C = 2.0 mA, I_B = 0)	$V_{(BR)CEO}$	50	–	–	Vdc
ON CHARACTERISTICS					
DC Current Gain (Note 5) (I_C = 5.0 mA, V_{CE} = 10 V)	h_{FE}	160	250	–	
Collector−Emitter Saturation Voltage (Note 5) (I_C = 10 mA, I_B = 0.3 mA)	$V_{CE(sat)}$	–	–	0.25	Vdc
Input Voltage (off) (V_{CE} = 5.0 V, I_C = 100 μA)	$V_{i(off)}$	–	0.6	0.5	Vdc
Input Voltage (on) (V_{CE} = 0.3 V, I_C = 10 mA)	$V_{i(on)}$	1.7	1.2	–	Vdc
Output Voltage (on) (V_{CC} = 5.0 V, V_B = 2.5 V, R_L = 1.0 kΩ)	V_{OL}	–	–	0.2	Vdc
Output Voltage (off) (V_{CC} = 5.0 V, V_B = 0.25 V, R_L = 1.0 kΩ)	V_{OH}	4.9	–	–	Vdc
Input Resistor	R1	7.0	10	13	kΩ
Resistor Ratio	R_1/R_2	–	–	–	

Product parametric performance is indicated in the Electrical Characteristics for the listed test conditions, unless otherwise noted. Product performance may not be indicated by the Electrical Characteristics if operated under different conditions.

5. Pulsed Condition: Pulse Width = 300 msec, Duty Cycle ≤ 2%.

TYPICAL CHARACTERISTICS
MUN2115, MMUN2115L, MUN5115, DTA114TE, DTA114TM3

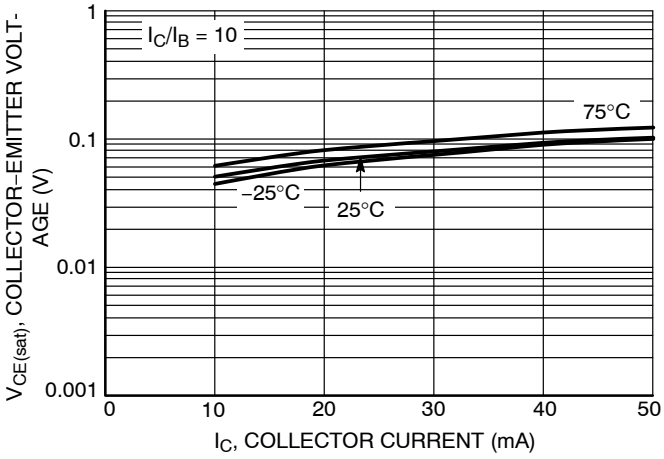


Figure 2. $V_{CE(sat)}$ vs. I_C

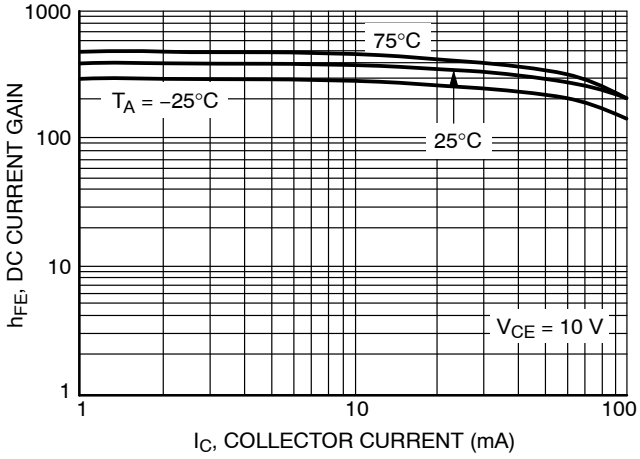


Figure 3. DC Current Gain

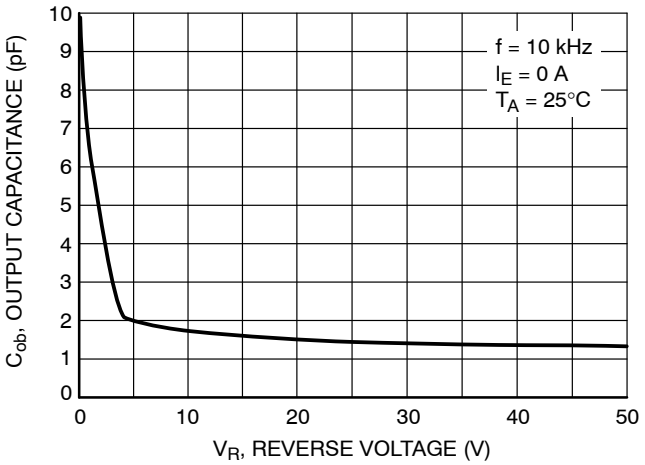


Figure 4. Output Capacitance

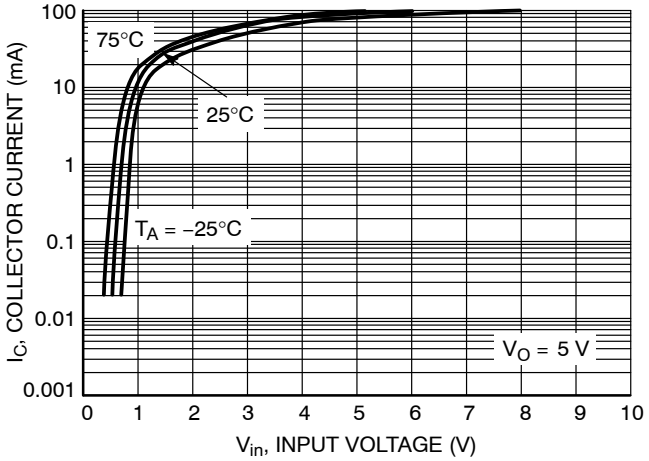


Figure 5. Output Current vs. Input Voltage

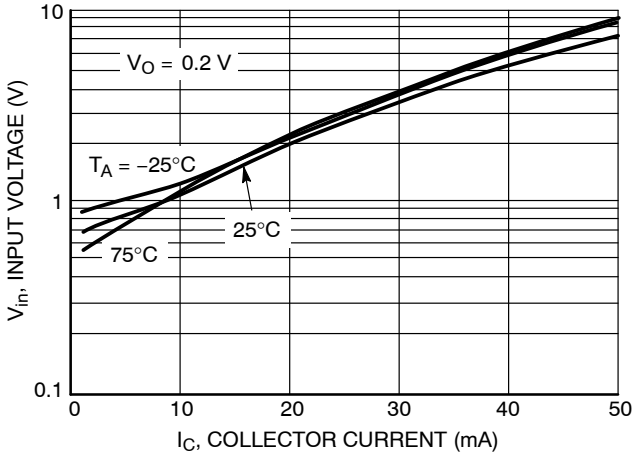


Figure 6. Input Voltage vs. Output Current

TYPICAL CHARACTERISTICS – NSBA114TF3

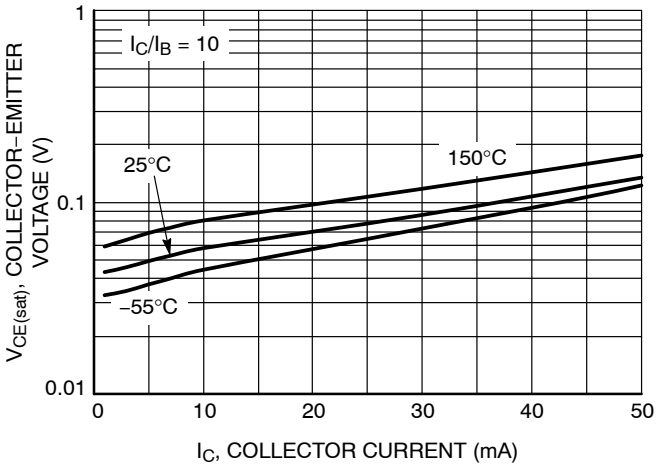


Figure 7. $V_{CE(sat)}$ vs. I_C

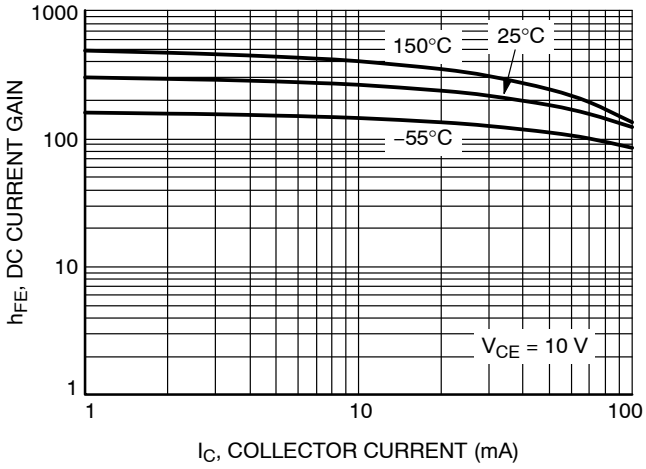


Figure 8. DC Current Gain

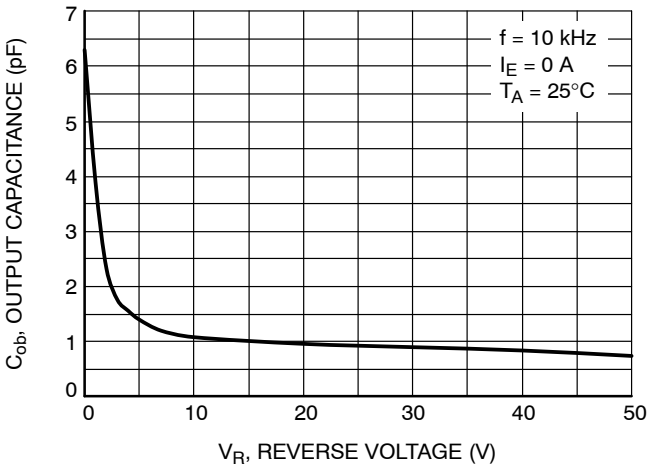


Figure 9. Output Capacitance

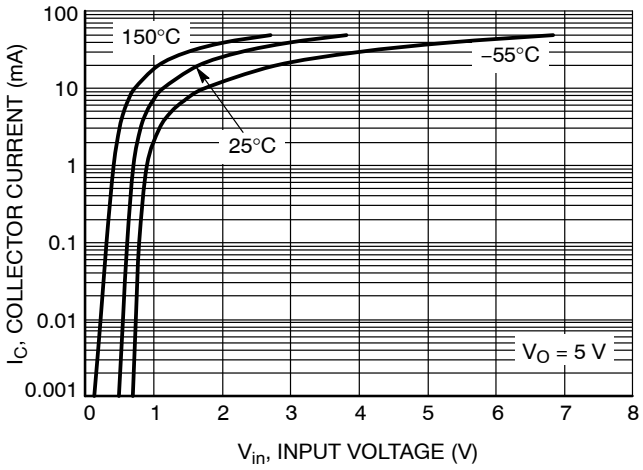


Figure 10. Output Current vs. Input Voltage

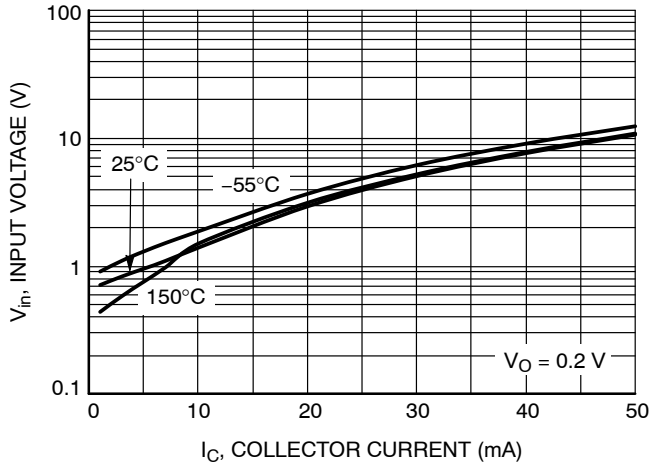
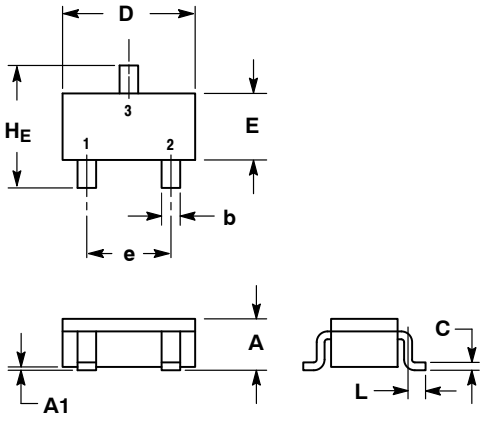


Figure 11. Input Voltage vs. Output Current

PACKAGE DIMENSIONS

SC−59
CASE 318D−04
ISSUE H

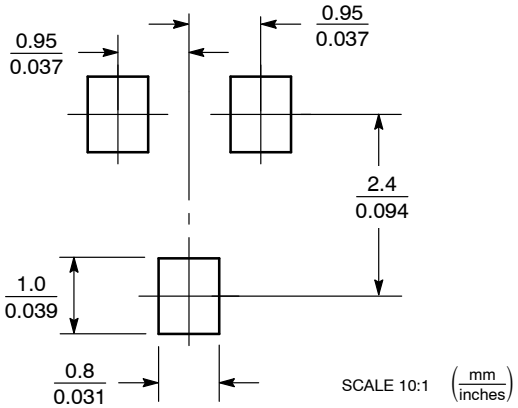


NOTES:
1. DIMENSIONING AND TOLERANCING PER ANSI Y14.5M, 1982.
2. CONTROLLING DIMENSION: MILLIMETER.

	MILLIMETERS			INCHES		
DIM	MIN	NOM	MAX	MIN	NOM	MAX
A	1.00	1.15	1.30	0.039	0.045	0.051
A1	0.01	0.06	0.10	0.001	0.002	0.004
b	0.35	0.43	0.50	0.014	0.017	0.020
c	0.09	0.14	0.18	0.003	0.005	0.007
D	2.70	2.90	3.10	0.106	0.114	0.122
E	1.30	1.50	1.70	0.051	0.059	0.067
e	1.70	1.90	2.10	0.067	0.075	0.083
L	0.20	0.40	0.60	0.008	0.016	0.024
H_E	2.50	2.80	3.00	0.099	0.110	0.118

STYLE 1:
PIN 1. BASE
2. EMITTER
3. COLLECTOR

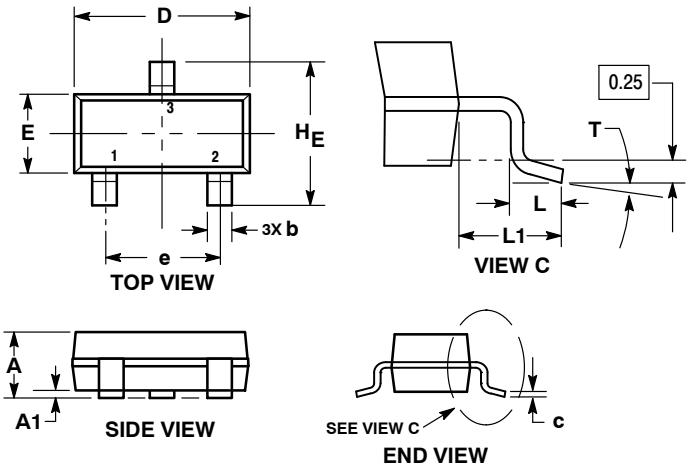
SOLDERING FOOTPRINT*



*For additional information on our Pb−Free strategy and soldering details, please download the ON Semiconductor Soldering and Mounting Techniques Reference Manual, SOLDERRM/D.

PACKAGE DIMENSIONS

SOT−23 (TO−236)
CASE 318−08
ISSUE AR

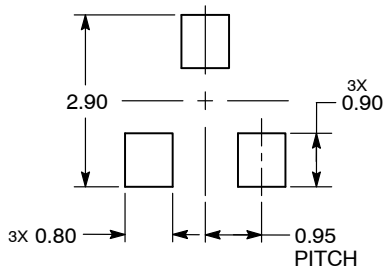


NOTES:
1. DIMENSIONING AND TOLERANCING PER ASME Y14.5M, 1994.
2. CONTROLLING DIMENSION: MILLIMETERS.
3. MAXIMUM LEAD THICKNESS INCLUDES LEAD FINISH. MINIMUM LEAD THICKNESS IS THE MINIMUM THICKNESS OF THE BASE MATERIAL.
4. DIMENSIONS D AND E DO NOT INCLUDE MOLD FLASH, PROTRUSIONS, OR GATE BURRS.

	MILLIMETERS			INCHES		
DIM	MIN	NOM	MAX	MIN	NOM	MAX
A	0.89	1.00	1.11	0.035	0.039	0.044
A1	0.01	0.06	0.10	0.000	0.002	0.004
b	0.37	0.44	0.50	0.015	0.017	0.020
c	0.08	0.14	0.20	0.003	0.006	0.008
D	2.80	2.90	3.04	0.110	0.114	0.120
E	1.20	1.30	1.40	0.047	0.051	0.055
e	1.78	1.90	2.04	0.070	0.075	0.080
L	0.30	0.43	0.55	0.012	0.017	0.022
L1	0.35	0.54	0.69	0.014	0.021	0.027
H_E	2.10	2.40	2.64	0.083	0.094	0.104
T	0°	−−−	10 °	0 °	−−−	10 °

STYLE 6:
PIN 1. BASE
2. EMITTER
3. COLLECTOR

RECOMMENDED SOLDERING FOOTPRINT*

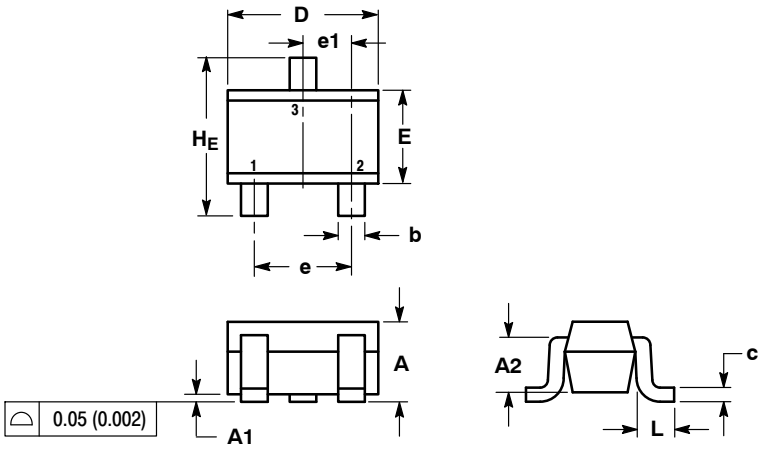


DIMENSIONS: MILLIMETERS

*For additional information on our Pb−Free strategy and soldering details, please download the ON Semiconductor Soldering and Mounting Techniques Reference Manual, SOLDERRM/D.

PACKAGE DIMENSIONS

SC−70 (SOT−323)
CASE 419−04
ISSUE N

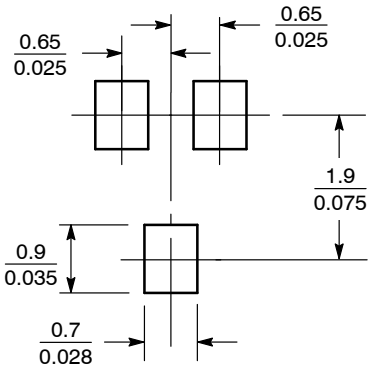


NOTES:
1. DIMENSIONING AND TOLERANCING PER ANSI Y14.5M, 1982.
2. CONTROLLING DIMENSION: INCH.

	MILLIMETERS			INCHES		
DIM	MIN	NOM	MAX	MIN	NOM	MAX
A	0.80	0.90	1.00	0.032	0.035	0.040
A1	0.00	0.05	0.10	0.000	0.002	0.004
A2		0.70 REF			0.028 REF	
b	0.30	0.35	0.40	0.012	0.014	0.016
c	0.10	0.18	0.25	0.004	0.007	0.010
D	1.80	2.10	2.20	0.071	0.083	0.087
E	1.15	1.24	1.35	0.045	0.049	0.053
e	1.20	1.30	1.40	0.047	0.051	0.055
e1		0.65 BSC			0.026 BSC	
L	0.20	0.38	0.56	0.008	0.015	0.022
H_E	2.00	2.10	2.40	0.079	0.083	0.095

STYLE 3:
PIN 1. BASE
2. EMITTER
3. COLLECTOR

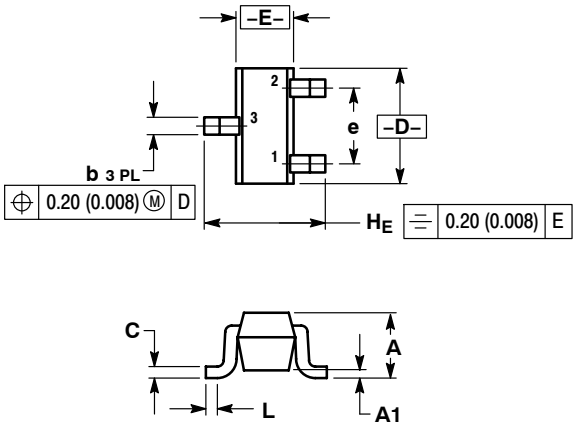
SOLDERING FOOTPRINT*



*For additional information on our Pb−Free strategy and soldering details, please download the ON Semiconductor Soldering and Mounting Techniques Reference Manual, SOLDERRM/D.

PACKAGE DIMENSIONS

SC−75/SOT−416
CASE 463
ISSUE G

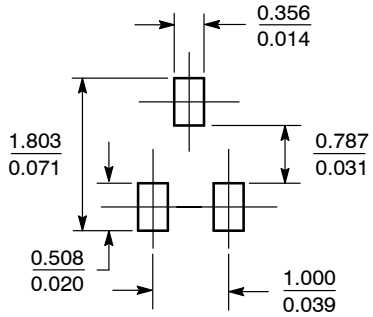


NOTES:
1. DIMENSIONING AND TOLERANCING PER ANSI Y14.5M, 1982.
2. CONTROLLING DIMENSION: MILLIMETER.

	MILLIMETERS			INCHES		
DIM	MIN	NOM	MAX	MIN	NOM	MAX
A	0.70	0.80	0.90	0.027	0.031	0.035
A1	0.00	0.05	0.10	0.000	0.002	0.004
b	0.15	0.20	0.30	0.006	0.008	0.012
C	0.10	0.15	0.25	0.004	0.006	0.010
D	1.55	1.60	1.65	0.059	0.063	0.067
E	0.70	0.80	0.90	0.027	0.031	0.035
e	1.00 BSC			0.04 BSC		
L	0.10	0.15	0.20	0.004	0.006	0.008
H_E	1.50	1.60	1.70	0.061	0.063	0.065

STYLE 1:
PIN 1. BASE
2. EMITTER
3. COLLECTOR

SOLDERING FOOTPRINT*

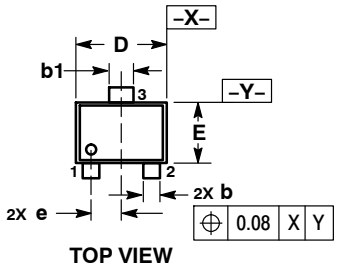


SCALE 10:1 $\left(\frac{\text{mm}}{\text{inches}}\right)$

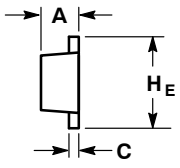
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PACKAGE DIMENSIONS

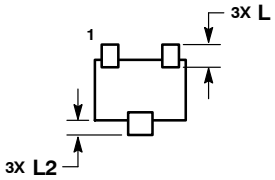
SOT−723
CASE 631AA
ISSUE D



TOP VIEW



SIDE VIEW



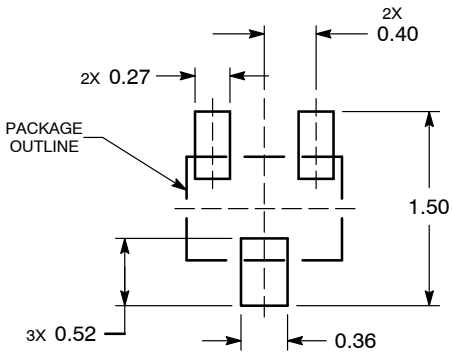
BOTTOM VIEW

NOTES:
1. DIMENSIONING AND TOLERANCING PER ASME Y14.5M, 1994.
2. CONTROLLING DIMENSION: MILLIMETERS.
3. MAXIMUM LEAD THICKNESS INCLUDES LEAD FINISH. MINIMUM LEAD THICKNESS IS THE MINIMUM THICKNESS OF BASE MATERIAL.
4. DIMENSIONS D AND E DO NOT INCLUDE MOLD FLASH, PROTRUSIONS OR GATE BURRS.

	MILLIMETERS		
DIM	MIN	NOM	MAX
A	0.45	0.50	0.55
b	0.15	0.21	0.27
b1	0.25	0.31	0.37
C	0.07	0.12	0.17
D	1.15	1.20	1.25
E	0.75	0.80	0.85
e		0.40 BSC	
H E	1.15	1.20	1.25
L		0.29 REF	
L2	0.15	0.20	0.25

STYLE 1:
PIN 1. BASE
2. EMITTER
3. COLLECTOR

RECOMMENDED SOLDERING FOOTPRINT*

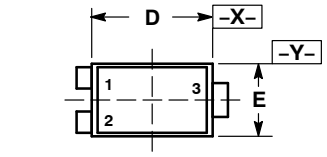


DIMENSIONS: MILLIMETERS

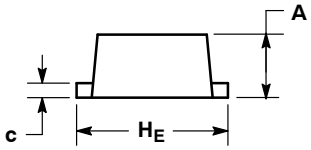
*For additional information on our Pb−Free strategy and soldering details, please download the ON Semiconductor Soldering and Mounting Techniques Reference Manual, SOLDERRM/D.

PACKAGE DIMENSIONS

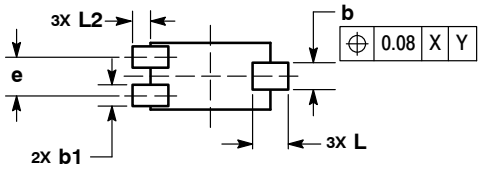
SOT−1123
CASE 524AA
ISSUE C



TOP VIEW



SIDE VIEW



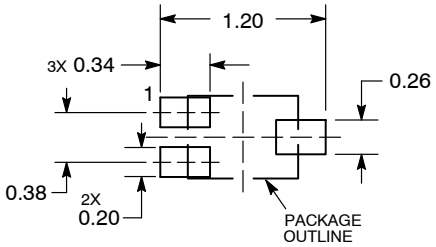
BOTTOM VIEW

NOTES:
1. DIMENSIONING AND TOLERANCING PER ASME Y14.5M, 1994.
2. CONTROLLING DIMENSION: MILLIMETERS.
3. MAXIMUM LEAD THICKNESS INCLUDES LEAD FINISH. MINIMUM LEAD THICKNESS IS THE MINIMUM THICKNESS OF BASE MATERIAL.
4. DIMENSIONS D AND E DO NOT INCLUDE MOLD FLASH, PROTRUSIONS, OR GATE BURRS.

	MILLIMETERS	
DIM	MIN	MAX
A	0.34	0.40
b	0.15	0.28
b1	0.10	0.20
c	0.07	0.17
D	0.75	0.85
E	0.55	0.65
e	0.35	0.40
H_E	0.95	1.05
L	0.185 REF	
L2	0.05	0.15

STYLE 1:
PIN 1. BASE
2. EMITTER
3. COLLECTOR

SOLDERING FOOTPRINT*



DIMENSIONS: MILLIMETERS

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